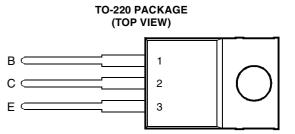
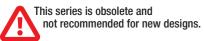
BD646, BD648, BD650, BD652 PNP SILICON POWER DARLINGTONS

BOURNS®

- Designed for Complementary Use with BD645, BD647, BD649 and BD651
- 62.5 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3V, 3 A





Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT	
	BD646		-80		
Collector-base voltage (I _E = 0)	BD648		-100	v	
	BD650	^V сво	-120		
	BD652		-140		
Collector-emitter voltage (I _B = 0)	BD646		-60		
	BD648	V _{CEO}	-80	V	
	BD650		-100		
	BD652		-120		
Emitter-base voltage		V _{EBO}	-5	V	
Continuous collector current			-8	A	
Peak collector current (see Note 1)			-12	А	
Continuous base current			-0.3	А	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			62.5	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			2	W	
Unclamped inductive load energy (see Note 4)			50	mJ	
Operating junction temperature range			-65 to +150	°C	
Storage temperature range			-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds		T _{stg} T _L	260	°C	

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$

2. Derate linearly to 150° C case temperature at the rate of 0.4 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -5 mA, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = -20 V.

PRODUCT INFORMATION

BD646, BD648, BD650, BD652 PNP SILICON POWER DARLINGTONS



electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER		TEST CO	ONDITIONS		MIN	ТҮР	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -30 mA	I _B = 0	(see Note 5)	BD646 BD648 BD650	-60 -80 -100			v
					BD652	-120			
		V _{CE} = -30 V	I _B = 0		BD646			-0.5	
I _{CEO}	Collector-emitter	V _{CE} = -40 V	I _B = 0		BD648			-0.5	mA
010	cut-off current	$V_{CE} = -50 V$	I _B = 0		BD650			-0.5	
		$V_{CE} = -60 V$ $V_{CB} = -60 V$	$I_{\rm B} = 0$ $I_{\rm F} = 0$		BD652 BD646			-0.5 -0.2	
	Collector cut-off	$V_{CB} = -80 V$ $V_{CB} = -80 V$	I _E = 0 I _F = 0		BD648			-0.2	
		$V_{CB} = -100 V$	$I_{\rm E} = 0$		BD650			-0.2	
			$I_{\rm E} = 0$		BD652			-0.2	mA
I _{СВО}	current		I _E = 0	T _C = 150°C	BD646			-2.0	
		$V_{CB} = -50 V$	-	T _C = 150°C	BD648			-2.0	
		V _{CB} = -60 V	$I_E = 0$	T _C = 150°C	BD650			-2.0	
		V _{CB} = -70 V	$I_E = 0$	$T_{C} = 150^{\circ}C$	BD652			-2.0	
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	$I_{\rm C} = 0$	(see Notes 5 and	6)			-5	mA
h _{FE}	Forward current transfer ratio	V _{CE} = -3 V	I _C = -3 A	(see Notes 5 and	.6)	750			
V _{CE(sat)}	Collector-emitter saturation voltage	$I_B = -12 \text{ mA}$ $I_B = -50 \text{ mA}$	0	(see Notes 5 and	6)			-2 -2.5	V
V _{BE(sat)}	Base-emitter saturation voltage	I _B = -50 mA	I _C = -5 A	(see Notes 5 and	6)			-3	V
V _{BE(on)}	Base-emitter voltage	V _{CE} = -3 V	I _C = -3 A	(see Notes 5 and	6)			-2.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \ \mu$ s, duty cycle $\leq 2\%$.

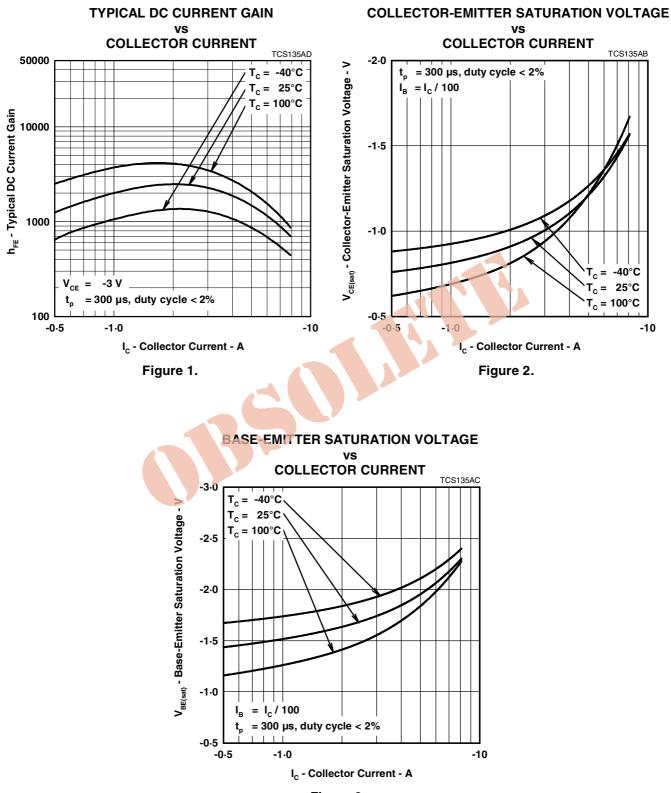
6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

ſ		PARAMETER	MIN	ТҮР	MAX	UNIT
ſ	R _{0JC} Junction to case thermal resistance				2.0	°C/W
Ī	$R_{ extsf{ heta}JA}$	Junction to free air thermal resistance			62.5	°C/W



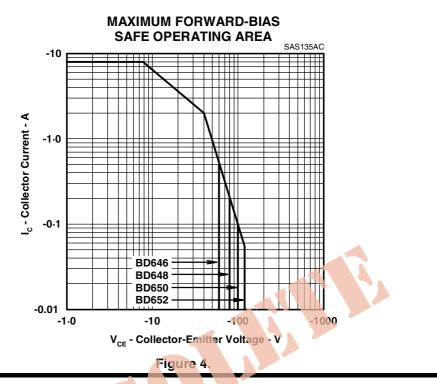
TYPICAL CHARACTERISTICS



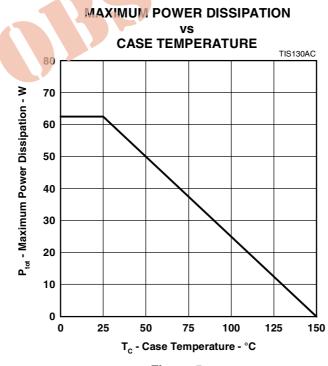


PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION





PRODUCT INFORMATION